

# 2SJ450

Silicon P-Channel MOS FET

# HITACHI

ADE-208-381  
1st. Edition

## Application

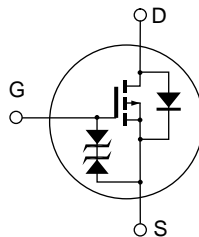
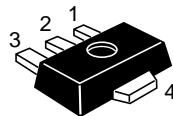
High speed power switching

## Features

- Low on-resistance.
- Low drive power
- High speed switching
- 2.5 V gate drive device.

## Outline

UPAK



1. Gate
2. Drain
3. Source
4. Drain

## Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DSS}$	-60	V
Gate to source voltage	$V_{GSS}$	±20	V
Drain current	$I_D$	-1	A
Drain peak current	$I_{D(pulse)}^{*1}$	-2	A
Drain peak current	$I_{DR}$	-1	A
Channel dissipation	$Pch^{*2}$	1	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1.  $PW \leq 100 \mu s$ , duty cycle  $\leq 10\%$

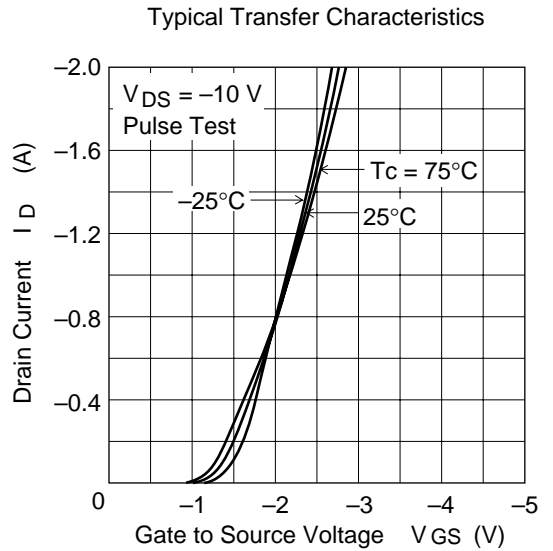
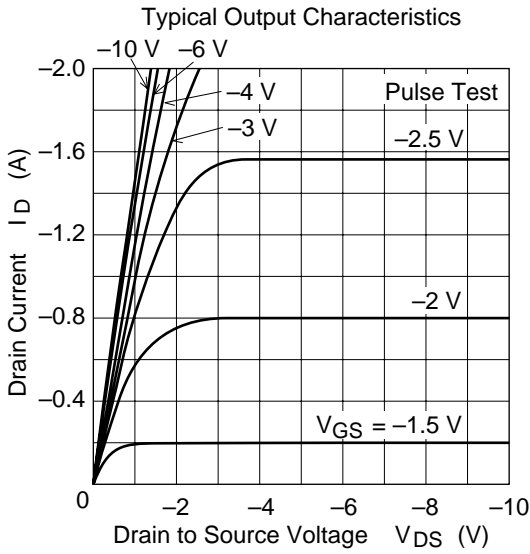
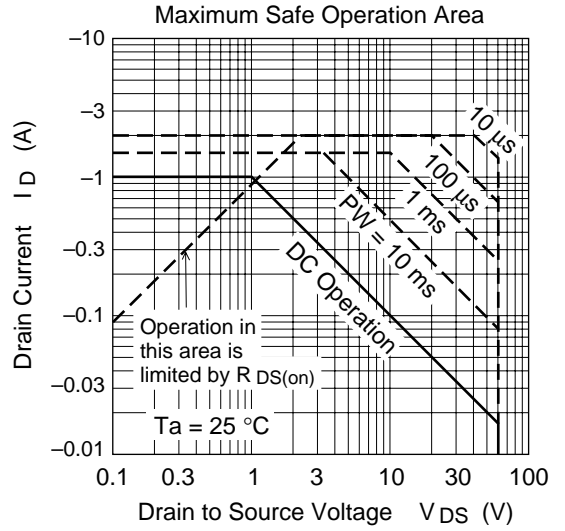
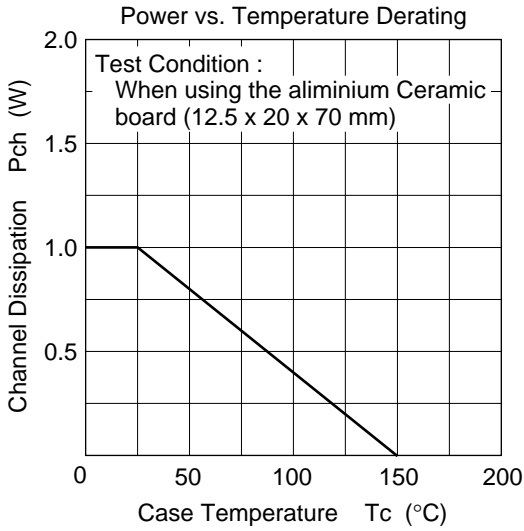
2. When using aluminium ceramic board (12.5 × 20 × 70 mm)

## Electrical Characteristics (Ta = 25°C)

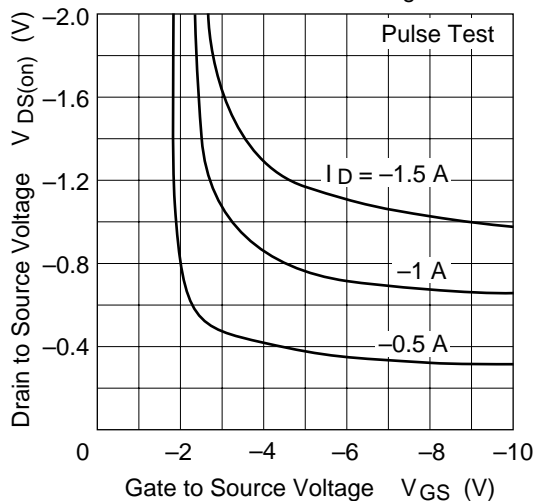
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-60	—	—	V	$I_D = -10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	$\pm 20$	—	—	V	$I_G = \pm 100 \text{ }\mu\text{A}, V_{DS} = 0$
Zero gate voltage drain current	$I_{DSS}$	—	—	-50	$\mu\text{A}$	$V_{DS} = -50 \text{ V}, V_{GS} = 0$
Gate to source leak current	$I_{GSS}$	—	—	$\pm 10$	$\mu\text{A}$	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-0.5	—	-1.5	V	$V_{DS} = -10 \text{ V}, I_D = -1 \text{ mA}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.85	1.2	$\Omega$	$I_D = -0.5 \text{ A}$ $V_{GS} = -4 \text{ V}^{*1}$
Static drain to source on state resistance	$R_{DS(on)}$	—	1.1	1.9	$\Omega$	$I_D = -0.3 \text{ A}$ $V_{GS} = -2.5 \text{ V}^{*1}$
Forward transfer admittance	$ y_{fs} $	0.6	1.0	—	S	$I_D = -0.5 \text{ A}$ $V_{DS} = -10 \text{ V}$
Input capacitance	$C_{iss}$	—	150	—	pF	$V_{DS} = -10 \text{ V}$
Output capacitance	$C_{oss}$	—	72	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	$C_{rss}$	—	24	—	pF	$f = 1 \text{ MHz}$
Turn-on delay time	$t_{d(on)}$	—	6	—	ns	$V_{GS} = -10 \text{ V}, I_D = -0.5 \text{ A}$
Rise time	$t_r$	—	9	—	ns	$R_L = 60 \text{ }\Omega$
Turn-off delay time	$t_{d(off)}$	—	50	—	ns	
Fall time	$t_f$	—	35	—	ns	
Body to drain diode forward voltage	$V_{DF}$	—	-0.9	—	V	$I_F = -1 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery time	$t_{rr}$	—	100	—	ns	$I_F = -1 \text{ A}, V_{GS} = 0$ $di_F/dt = 50 \text{ A}/\mu\text{s}$

Note: 1. Pulse Test

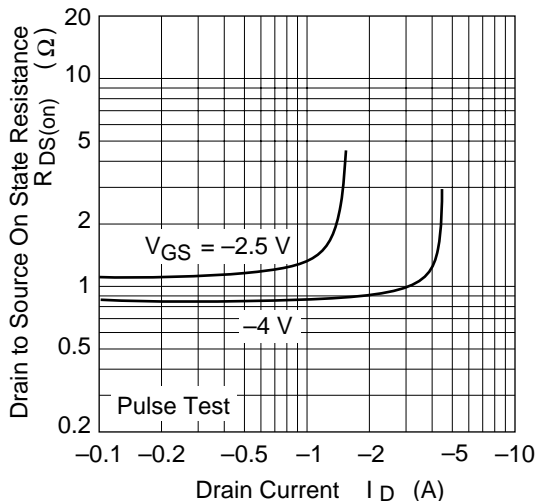
Marking is "UY".



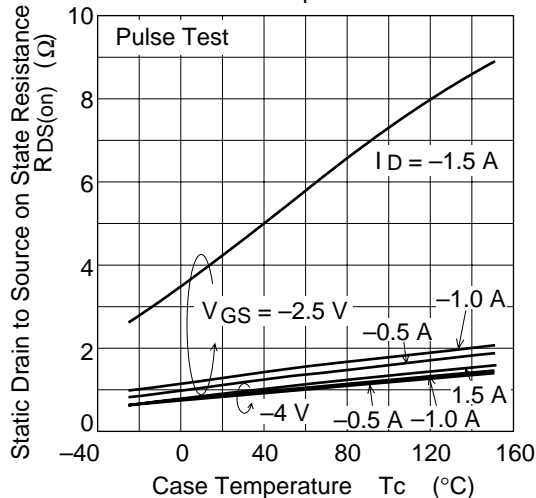
Drain to Source Saturation Voltage vs. Gate to Source Voltage



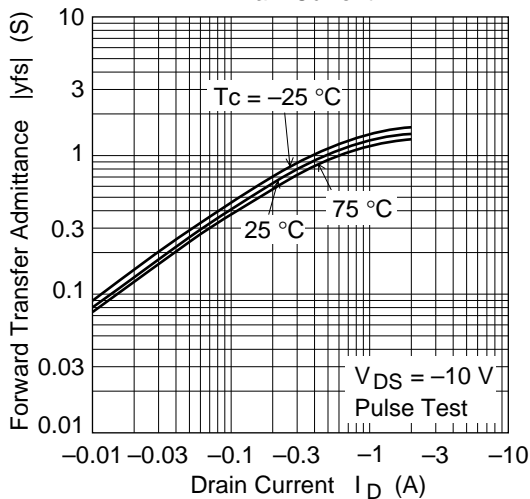
Static Drain to Source on State Resistance vs. Drain Current



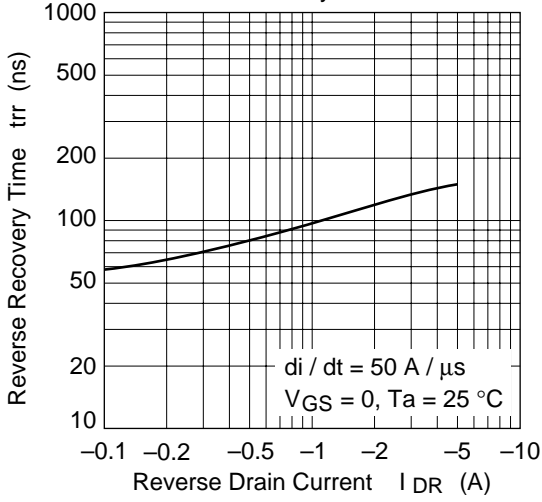
Static Drain to Source on State Resistance vs. Temperature



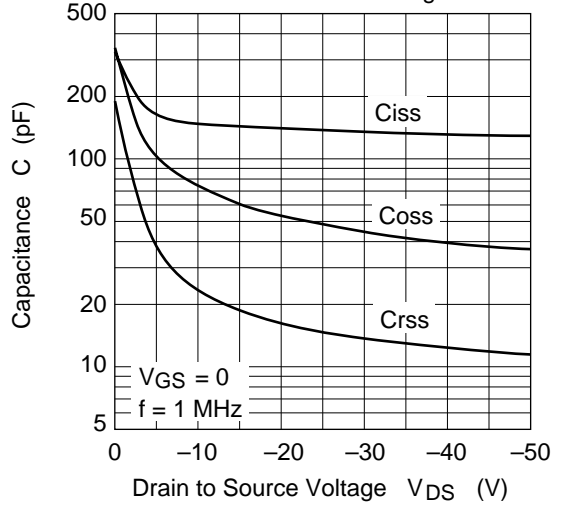
Forward Transfer Admittance vs. Drain Current



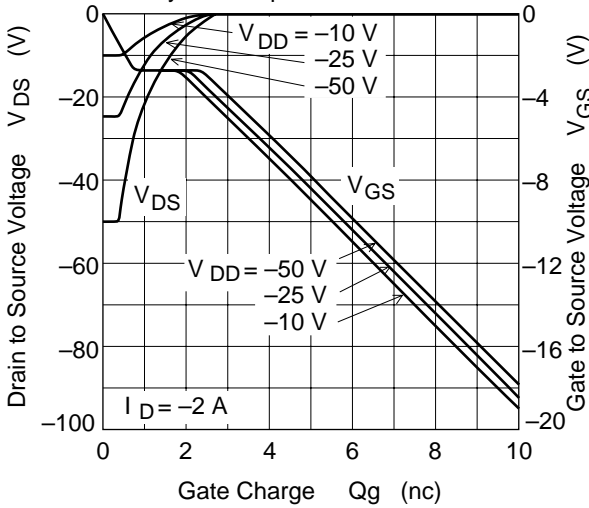
Body to Drain Diode Reverse Recovery Time



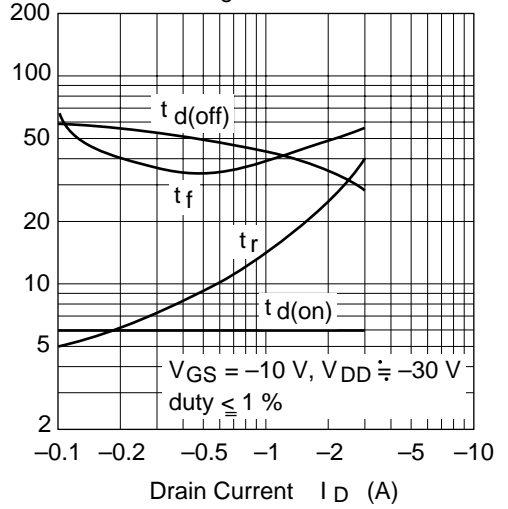
Typical Capacitance vs. Drain to Source Voltage

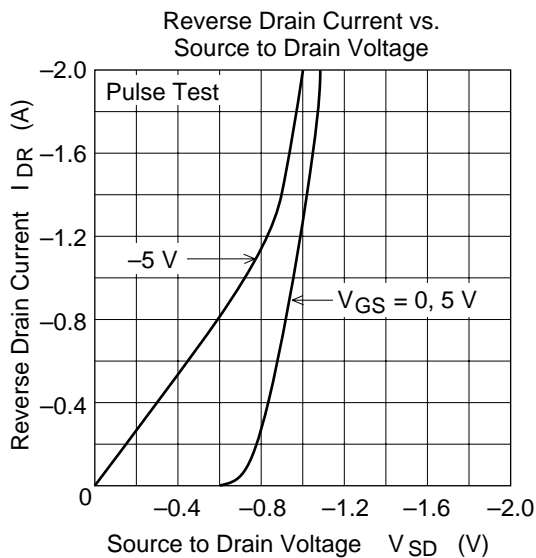


Dynamic Input Characteristics

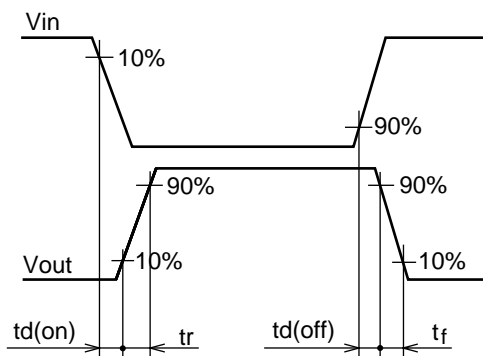
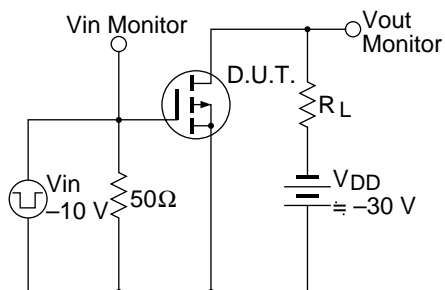


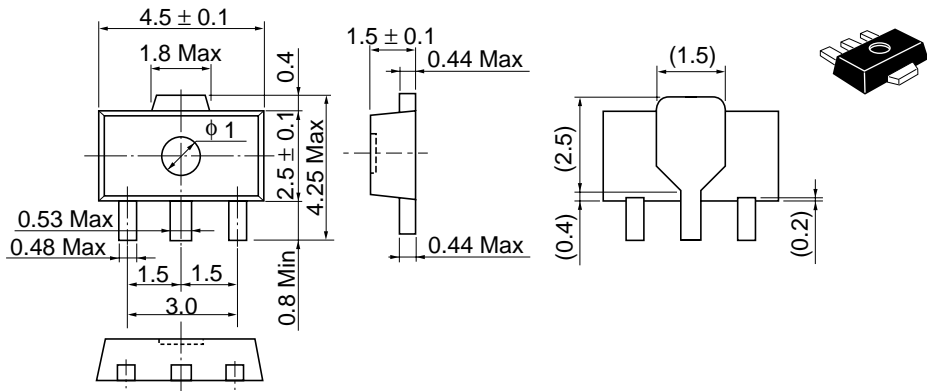
Switching Characteristics





Avalanche Test Circuit and Waveform





Hitachi Code	UPAK
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.050 g



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